PNP Silicon Epitaxial Planar Transistor

For switching and general purpose applications.

The transistor is subdivided into three groups P, Q and R, according to its DC current gain.



1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

	Symbol	Value	Unit
Collector Base Voltage	-V _{CBO}	40	V
Collector Emitter Voltage	-V _{CEO}	32	V
Emitter Base Voltage	-V _{EBO}	5	V
Collector Current	-I _C	500	mA
Power Dissipation	P _{tot}	200	mW
Junction Temperature	Tj	150	°C
Storage Temperature Range	Ts	-55 to +150	°C







Dated : 20/10/2005

MMBTSA1036

Characteristics at Tamb=25 °C

	Symbol	Min.	Тур.	Max.	Unit
DC Current Gain					
at -V _{CE} =3V, -I _C =100mA					
Current Gain Group P	h _{FE}	82	-	180	-
Q	h _{FE}	120	-	270	-
R	h _{FE}	180	-	390	-
Collector-base breakdown voltage	-V _{(BR)CBO}	40	-	-	V
at -I _C =100µA					
Collector-emitter breakdown voltage	-V _{(BR)CEO}	32	-	-	V
at -I _C =1mA					
Emitter-base breakdown voltage	-V _{(BR)EBO}	5	-	-	V
at -I _C =100µA					
Collector Cutoff Current					
at -V _{CB} =20V	-I _{CBO}	-	-	1	μA
Emitter Cutoff Current					
at -V _{EB} =4V	-I _{EBO}	-	-	1	μA
Collector Saturation Voltage					
at -I _C =300mA, -I _B =30mA	-V _{CE(sat)}	-	-	0.6	V
Transition Frequency					
at -V _{CE} =5V, -I _E =20mA, f=100MHz	f⊤	-	200	-	MHz
Collector Output Capacitance					
at -V _{CB} =10V, f=1MHz	Cob	-	7	-	pF





